华润微电子(重庆)有限公司

CRTT240N20N

Trench N-MOSFET 200V, 21mΩ, 65A

Features

- Uses CRM(CQ) advanced Trench technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent Q_gx$R_{DS(on)}$ product(FOM)
- Qualified according to JEDEC criteria

Applications

- Motor control and drive
- Battery management
- UPS (Uninterrupible Power Supplies)

Product Summary

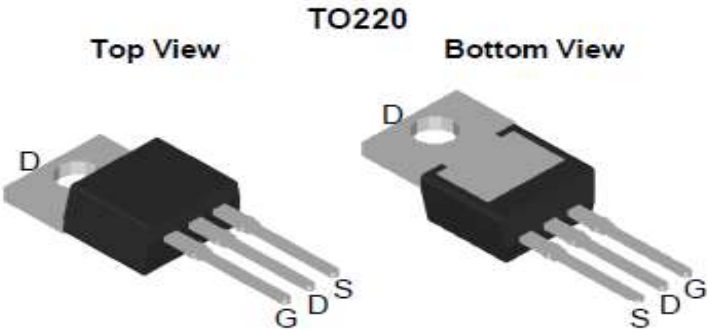
V_{DS}	200V
$R_{DS(on)\ typ.}$	21mΩ
I_D	65A

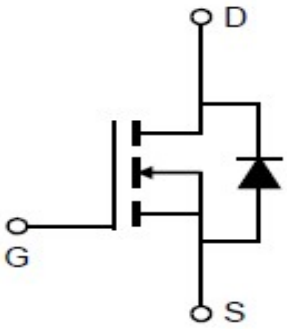
100% DVDS Tested

100% Avalanche Tested

RoHS

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Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRTT240N20N	CRTT240N20N	TO-220	Tube	N/A	N/A	50pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	200	V
Continuous drain current T_C = 25°C (Silicon limit) T_C = 25°C (Package limit) T_C = 100°C (Silicon limit)	I_D	 65 160 41	A
Pulsed drain current (T_C = 25°C, t_p limited by T_{jmax})	$I_{D\ pulse}$	260	A
Avalanche energy, single pulse (L=0.5mH, Rg=25Ω)	E_{AS}	150	mJ
Gate-Source voltage	V_{GS}	±20	V
Power dissipation (T_C = 25°C)	P_{tot}	278	W
Operating junction and storage temperature	T_j , T_{stg}	-55...+150	°C
Soldering temperature, wave soldering only allowed at leads (1.6mm from case for 10s)	T_{sold}	260	°C

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Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction – case.	R_{thJC}	0.45	°C/W
Thermal resistance, junction – ambient(min. footprint)	R_{thJA}*	62	

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Static Characteristic						
Drain-source breakdown voltage	BV_{DSS}	200	-	-	V	V_{GS}=0V, I_D=250uA
Gate threshold voltage	$V_{GS(th)}$	3.0	4.0	5.0	V	V_{DS}=V_{GS},I_D=250uA
Zero gate voltage drain current	I_{DSS}	- -	0.2 -	10 100	μA	V_{DS}=200V,V_{GS}=0V T_j=25°C T_j=150°C
Gate-source leakage current	I_{GSS}	-	±1	±100	nA	V_{GS}=±20V,V_{DS}=0V
Drain-source on-state resistance	$R_{DS(on)}$	- -	21 50	26 65	mΩ	V_{GS}=10V, I_D=30A, T_j=25°C T_j=150°C
Transconductance	g_{fs}	-	77	-	S	V_{DS}=5V,I_D=30A
Dynamic Characteristic						
Input Capacitance	C_{iss}	-	4190	-	pF	V_{GS}=0V, V_{DS}=100V, f=1MHz
Output Capacitance	C_{oss}	-	259	-		
Reverse Transfer Capacitance	C_{rss}	-	41	-		
Gate Total Charge	Q_G	-	74	-	nC	V_{GS}=10V, V_{DS}=100V, I_D=30A, f=1MHz
Gate-Source charge	Q_{gs}	-	28	-		
Gate-Drain charge	Q_{gd}	-	23	-		
Turn-on delay time	$t_{d(on)}$	-	28	-	ns	V_{GS}=10V, V_{DD}=100V, R_{G_ext}=2.7Ω
Rise time	t_r	-	76	-		
Turn-off delay time	$t_{d(off)}$	-	63	-		
Fall time	t_f	-	55	-		
Gate resistance	R_G	-	5	-	Ω	V_{GS}=0V, V_{DS}=0V, f=1MHz

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	0.8	1.3	V	V_{GS}=0V,I_{SD}=30A
Body Diode Forward Current	I_S			65	A	T_C = 25°C
Body Diode Reverse Recovery Time	t_{rr}	-	109	-	ns	I_F=30A, dI/dt=100A/μs
Body Diode Reverse Recovery Charge	Q_{rr}	-	587	-	nC	

*The value of R_{thJA} is measured by placing the device in a still air box which is one cubic foot.

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Typical Performance Characteristics

Fig 1: Output Characteristics

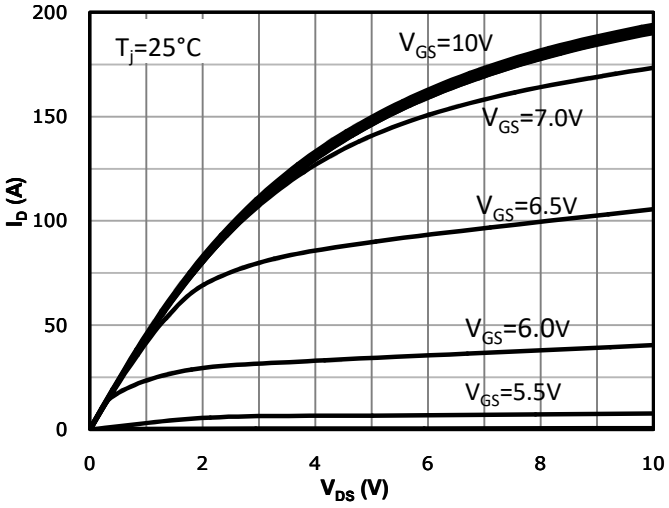


Fig 2: Transfer Characteristics

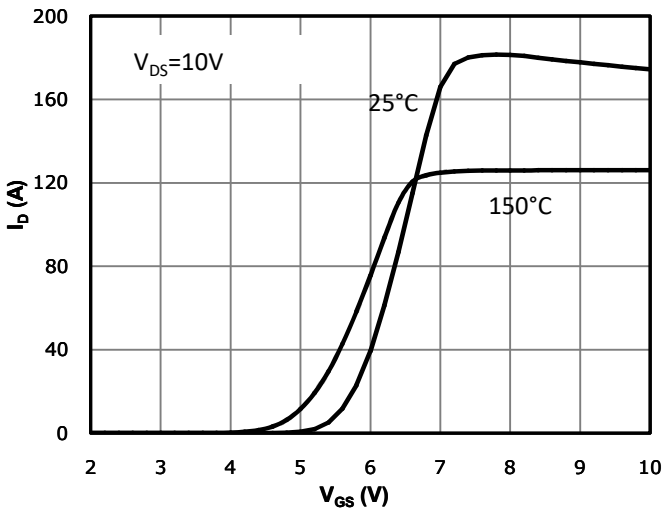


Fig 3: Rds(on) vs Drain Current and Gate Voltage

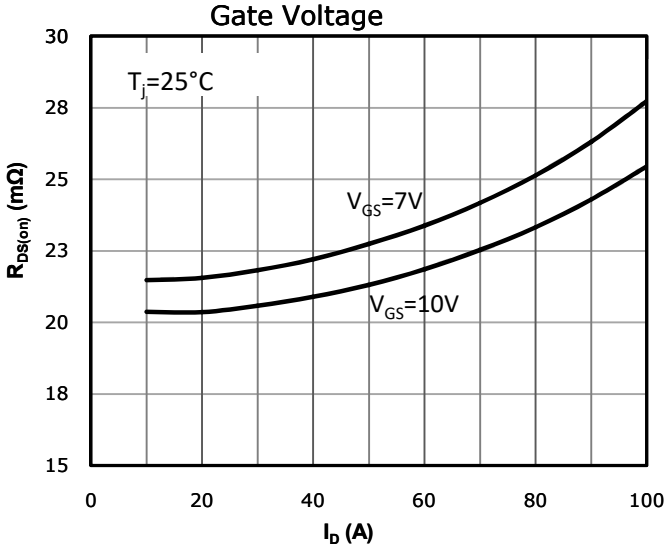


Fig 4: Rds(on) vs Gate Voltage

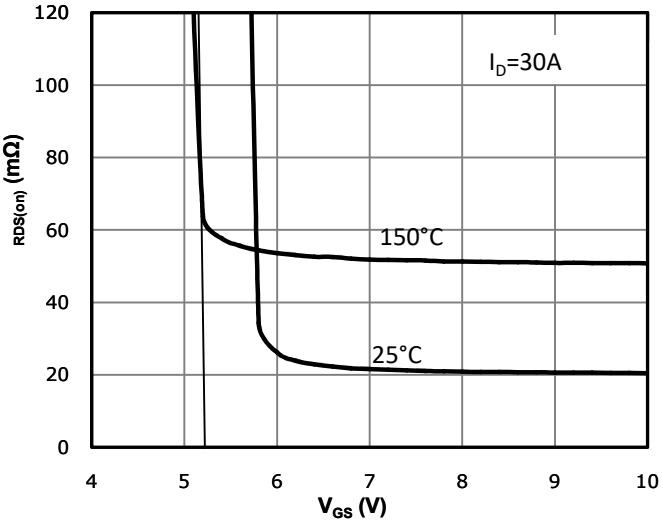


Fig 5: Rds(on) vs. Temperature

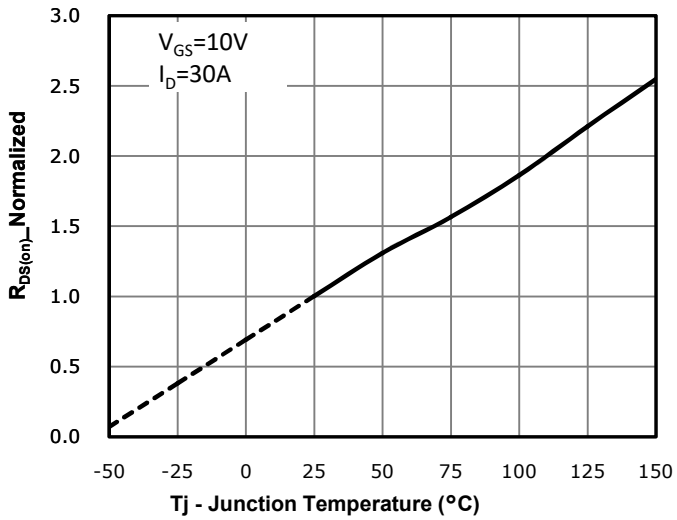


Fig 6: Capacitance Characteristics

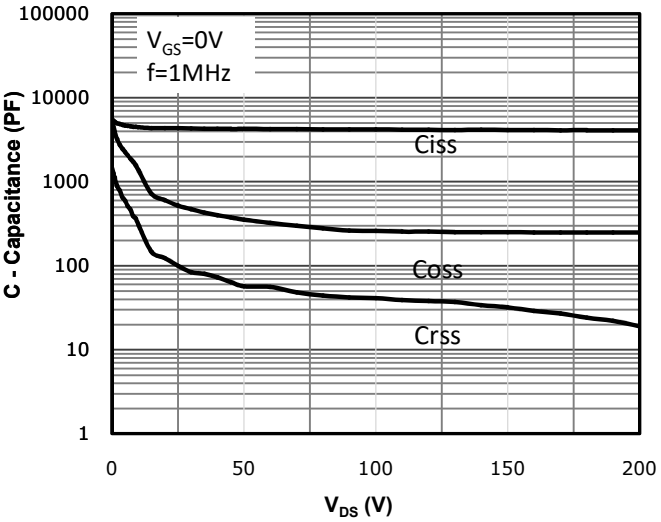


Fig 7: VTH vs. Temperature

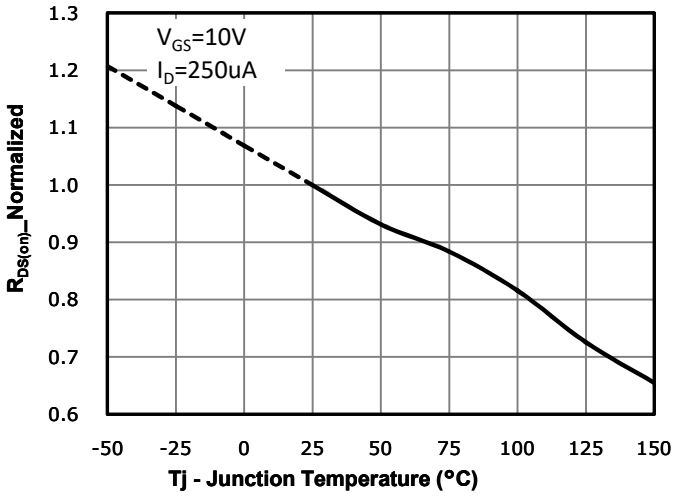


Fig 8: BVDS vs. Temperature

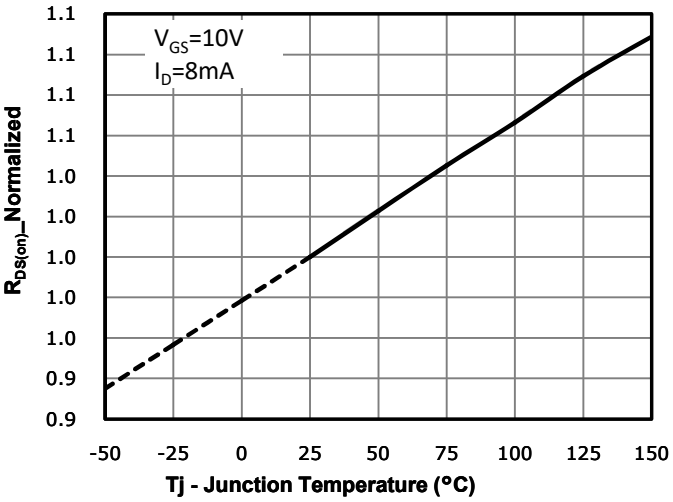


Fig 9: Gate Charge Characteristics

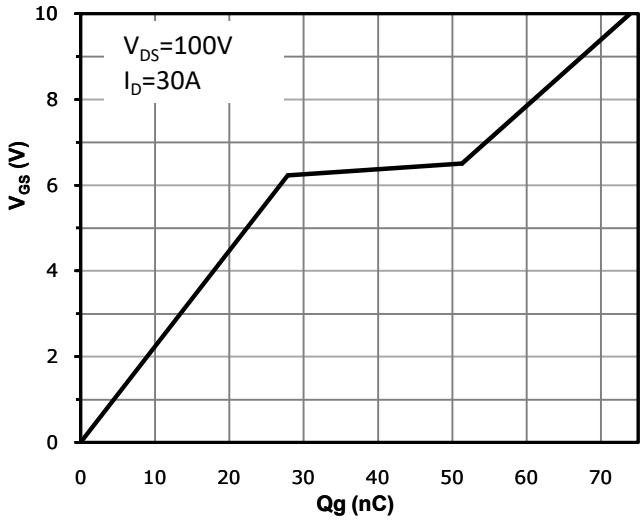


Fig 10: Body-diode Forward Characteristics

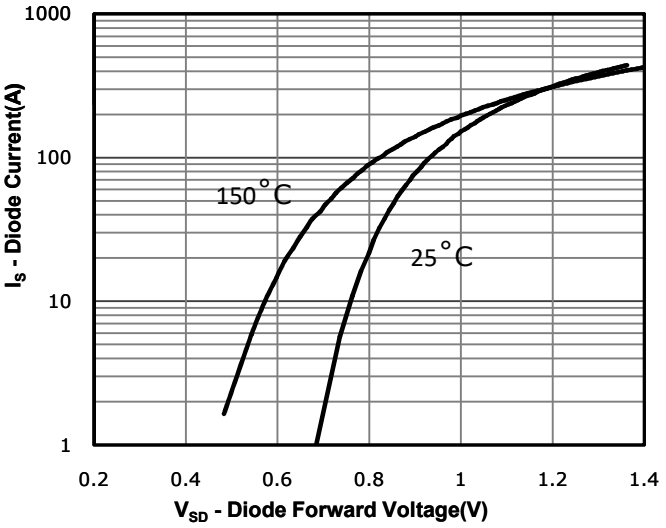


Fig 11: Power Dissipation

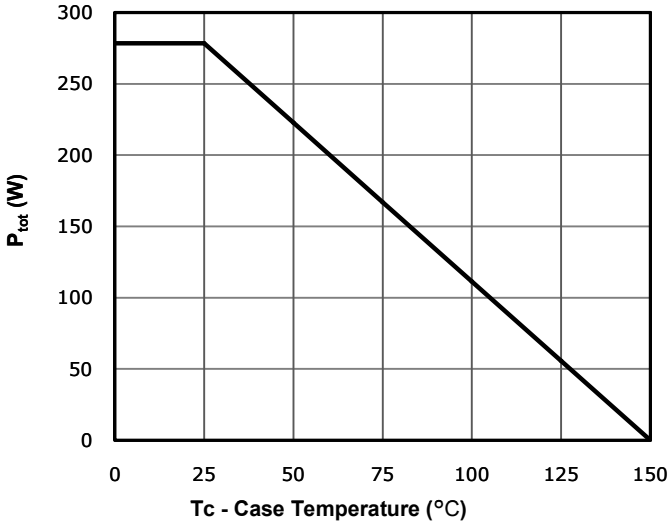
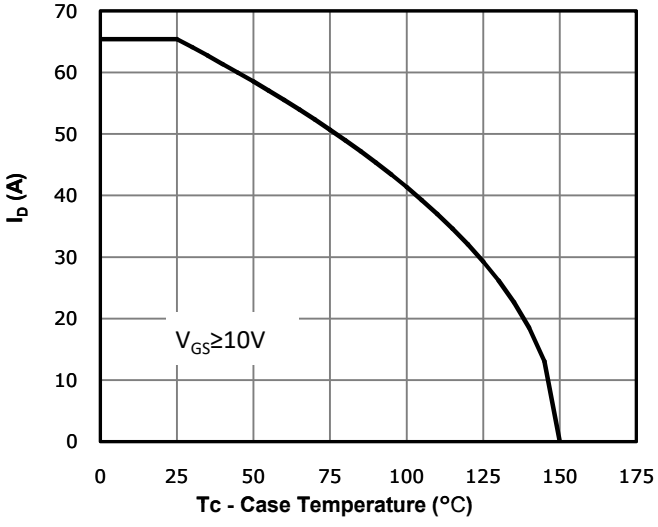


Fig 12: Drain Current Derating



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Fig 13: Safe Operating Area

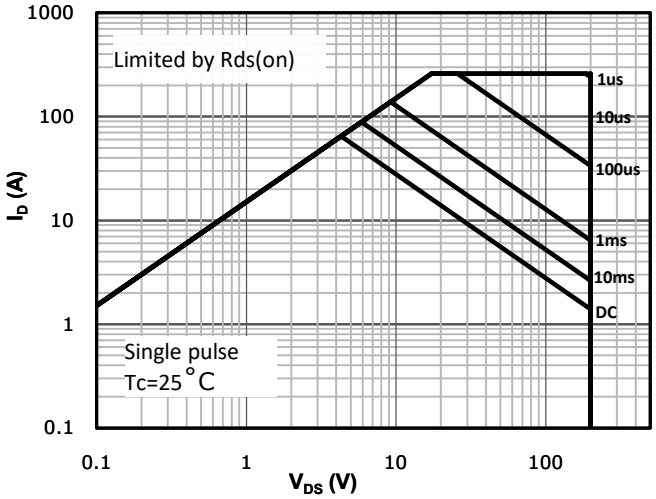
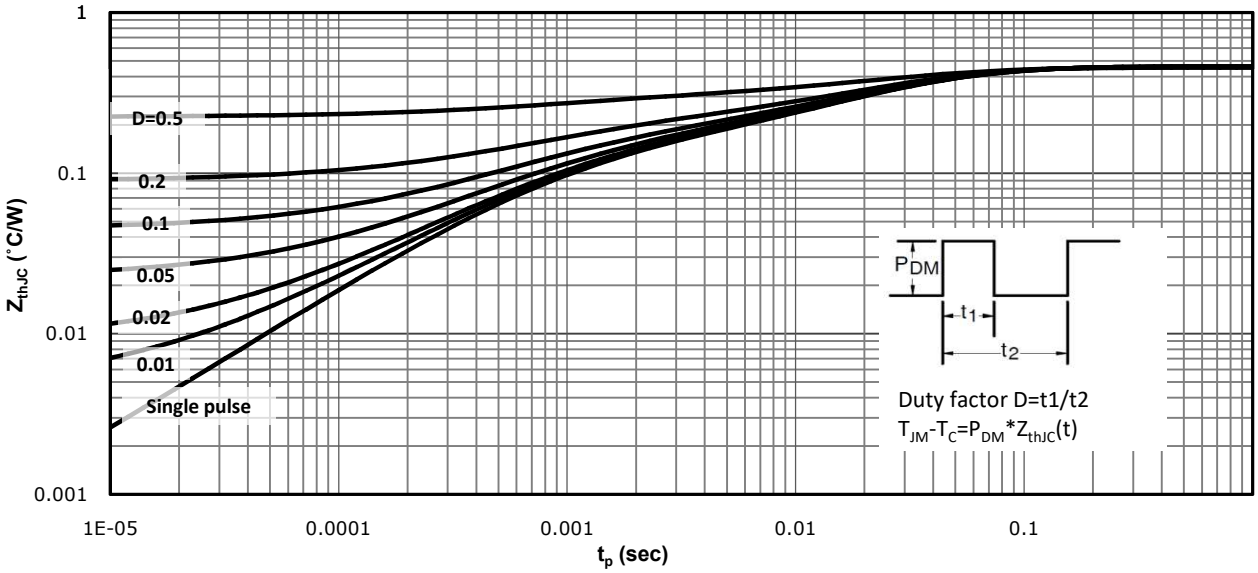
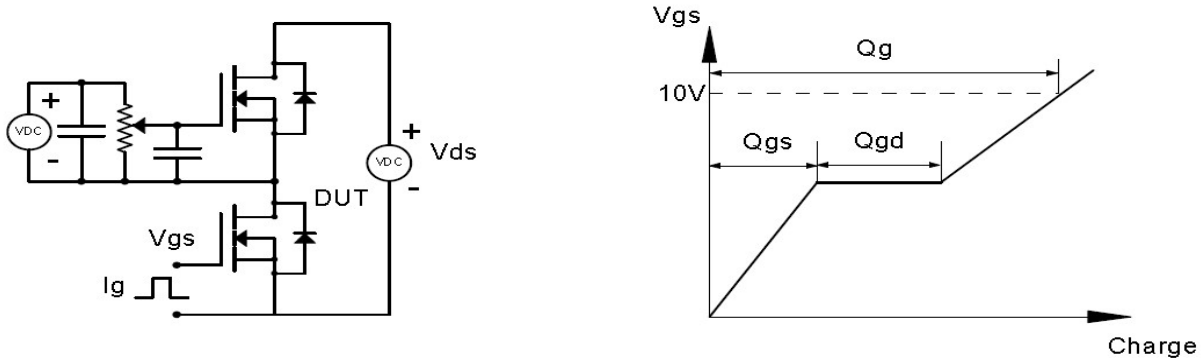


Fig 14: Max. Transient Thermal Impedance

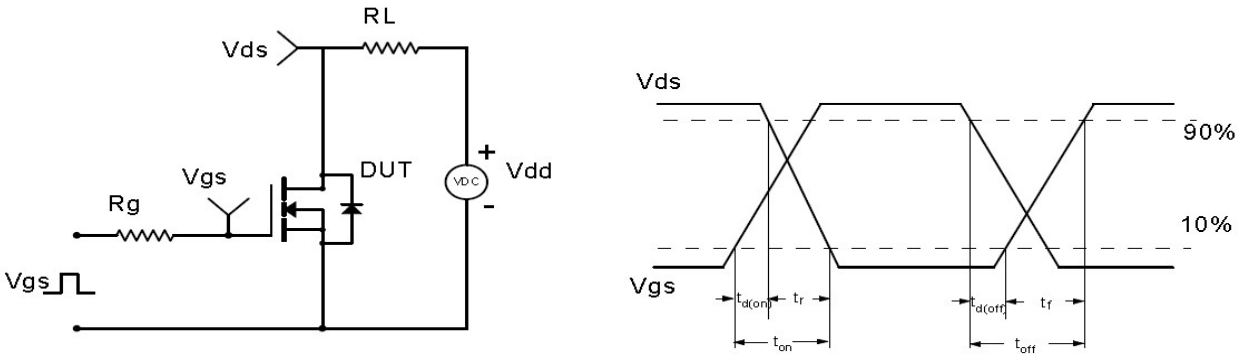


Test Circuit & Waveform

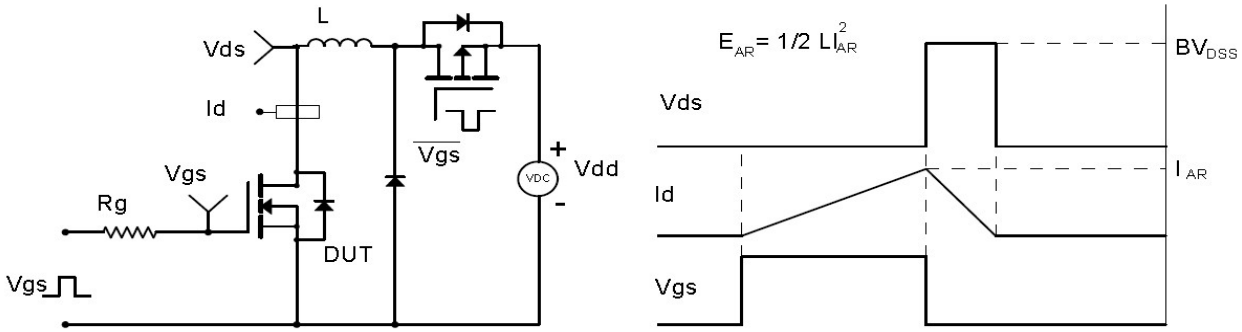
Gate Charge Test Circuit & Waveform



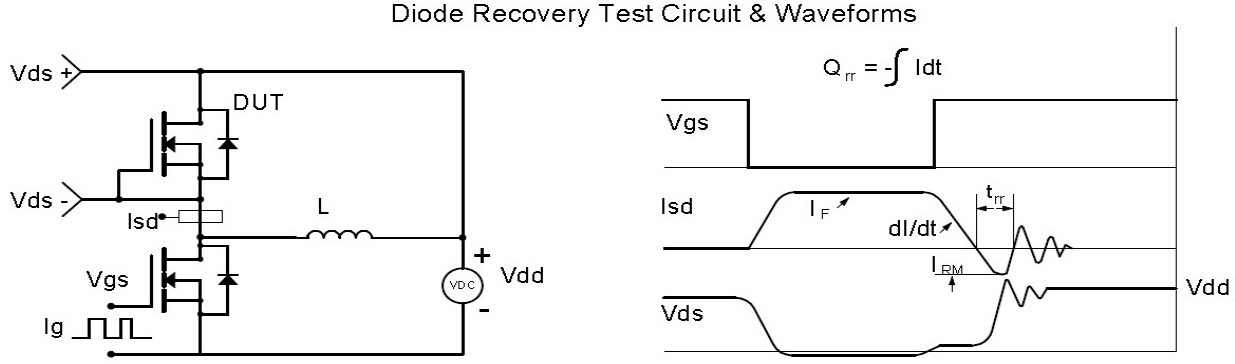
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

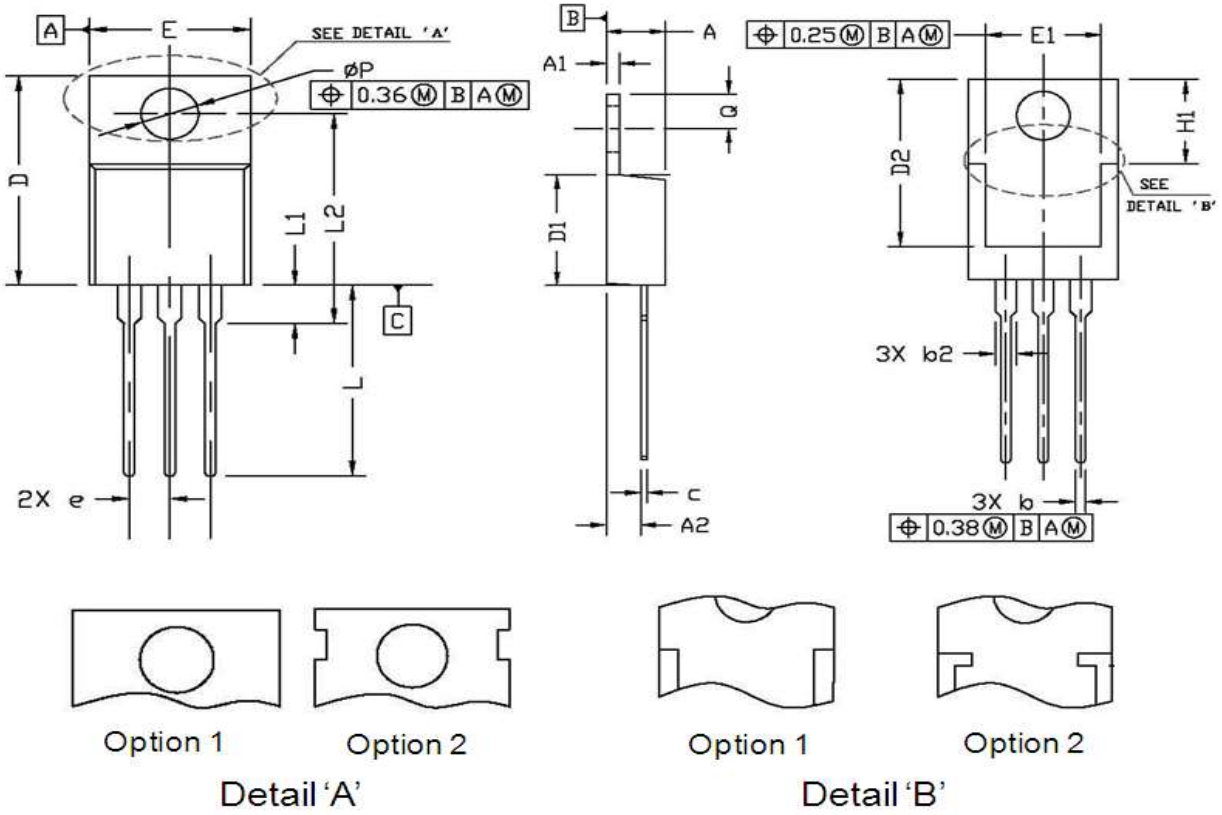


Diode Recovery Test Circuit & Waveforms



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Package Outline: TO-220



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.30	4.80	0.169	0.189
A1	1.20	1.45	0.047	0.057
A2	2.20	2.90	0.087	0.114
b	0.69	0.95	0.027	0.037
b2	1.00	1.60	0.039	0.063
c	0.33	0.65	0.013	0.026
D	14.70	16.20	0.579	0.638
D1	8.59	9.65	0.338	0.380
D2	11.75	13.60	0.463	0.535
e	2.54 BSC.		0.100 BSC.	
E	9.60	10.60	0.378	0.417
E1	7.00	8.89	0.276	0.350
H1	6.20	7.00	0.244	0.276
L	12.60	14.80	0.496	0.583
L1	2.70	3.80	0.106	0.150
L2	12.13	16.50	0.478	0.650
Q	2.40	3.10	0.094	0.122
P	3.50	3.95	0.138	0.156

Revision History

Revison	Date	Major changes
1.0	2022/1/17	Release of formal version

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qulified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semicondutor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.

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